

Single Line Bi-directional TVS Diode for EOS

DESCRIPTION

The GSD07DFMC TVS diode is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebooks, and PDA's. It offers superior electrical characteristics such as low clamping voltage, low leakage current and high surge capability. It is designed to protect sensitive electronic components which are connected to power lines, from over-stress caused by ESD (Electrostatic Discharge), EFT (Electrical Fast Transients) and Lighting.

The GSD07DFMC is in a SOD-123FL package and will protect one bidirectional line. It may be used to provide ESD protection up to $\pm 30 \text{kV}$ (Contact and air discharge) according to IEC61000-4-2, and withstand peak pulse current up to 200A (8/20µs) according to IEC61000-4-5.

FEATURES

±00KV (/ III)

- ♦Peak power dissipation:3600W (8/20µs)
- ♦Working voltages : 7V
- ♦Low leakage current
- ♦Low clamping voltage
- ♦ Solid-state silicon-avalanche technology

MACHANICAL DATA

- ♦SOD-123FL package
- ♦Flammability Rating: UL 94V-0
- ♦ High temperature soldering guaranteed: 260°C/10s
- ♦ Packaging: Tape and Reel
- ♦Reel size: 7 inch

ORDERING INFORMATION

Device: GSD07DFMCPackage: SOD-123FL

♦ Marking: AM.

♦ Material: Halogen free and RoHS compliant

♦ Packing: Tape & Reel

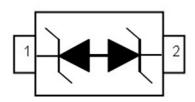
♦ Quantity per reel: 3,000pcs

APPLICATIONS

- ♦Power lines
- ♦Personal digital assistants (PDA's)
- ♦ Microprocessors based equipment
- ♦Notebooks, Desktops, and Servers
- ♦ Cell phone Handsets and Accessories
- ♦Portable Electronics
- ♦ Peripherals

PIN CONFIGURATION

PACKAGE OUTLINE







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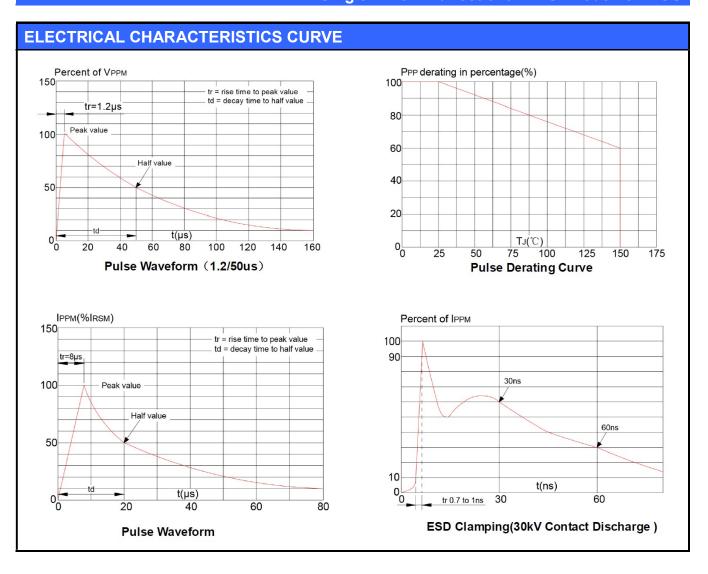
ABSOLUTE MAXIMUM RATING							
Symbol	Parameter	Value	Units				
V_{ESD}	ESD per IEC 61000-4-2 (Contact) ESD per IEC 61000-4-2 (Air)	±30 ±30	kV				
P _{PP}	Peak Pulse Power (8/20µs)	3600	W				
T _{OPT}	Operating Temperature	-55~125	°C				
T _{STG}	Storage Temperature	-55~150	°C				
TL	Lead Soldering Temperature	260(10sec)	°C				

ELECTRICAL CHARACTERISTICS (Tamb=25°C)									
Symbol	Parameter	Test Condition	Min	Тур	Max	Units			
V_{RWM}	Reverse Working Voltage				7.0	V			
V_{BR}	Reverse Breakdown Voltage	I _T = 1mA	8.0		10.0	V			
I _R	Reverse Leakage Current	V _{RWM} = 7V			1.0	μA			
I _{PP}	Peak Pulse Current	t _p = 8/20µs			200	Α			
V _C	Clamping Voltage	$I_{PP} = 200A, t_p = 8/20\mu s$			18	V			
Сл	Junction Capacitance	V _R = 0V, f = 1MHz		520	550	pF			

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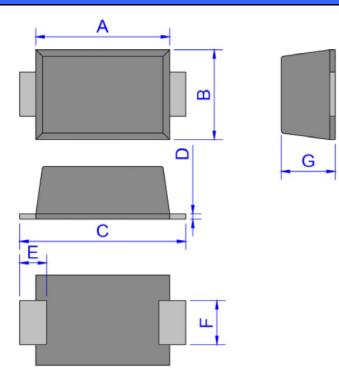


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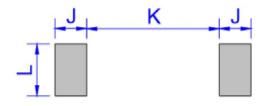
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SOD-123FL PACKAGE OUTLINE DIMENSIONS



	Dimensions				
Ref.	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
Α	2.60	3.00	0.102	0.118	
В	1.60	2.00	0.063	0.079	
С	3.45	3.95	0.136	0.156	
D	0.10	0.25	0.004	0.01	
E	0.3	0.9	0.012	0.035	
F	0.80	1.20	0.031	0.047	
G	0.95	1.35	0.037	0.053	
J	1.30		0.051		
K		1.70		0.067	
L	1.30		0.051		

Recommend Land Pattern (Unit: mm)



Note:

This recommended land pattern is for reference purpose only.

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